Improved InGaN/GaN light-emitting diodes with a p-GaN/n-GaN/p-GaN/n-GaN/p-GaN current-spreading layer: errata

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Abstract: The errata consists of the correction to one typo of the reach-through breakdown voltage for each p-GaN/n-GaN/p-GaN junction [Opt. Express 21, 4958-4969 (2013)].

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OCIS codes: (230.3670) Light-emitting diodes; (230.5590) Quantum-well, wire, dot devices; (160.6000) Semiconductor materials.

References and links

In the recent paper on p-GaN/n-GaN/p-GaN/n-GaN/p-GaN (PNPNP-GaN) proposed as a current spreading layer for InGaN/GaN light-emitting diodes [1], there is a typo in the equation of reach-through breakdown voltage in Section 3, where the term $W_N^2$ is mistakenly typed, as $W_N$ misses its quadratic power, and the correct form is $BV_{rt} = \frac{eN_P W_N^2}{2\varepsilon_f} e_0$.

We apologize for the confusion caused by the oversight. However, this correction neither affects the conclusions nor the device physics of this paper.